

BR2SB1198MCQ

Rev.A Apr.-2023

/ Descriptions

JF K) * \$* GE G Silicon PNP transistor in a SOT23-3 Plastic Package.

/ Features

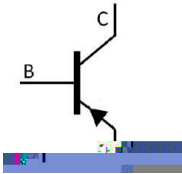
91) J; (. /) D : H AEC-Q101

High breakdown, low $V_{CE(sat)}$, complements the BR2SD1782MCQ, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

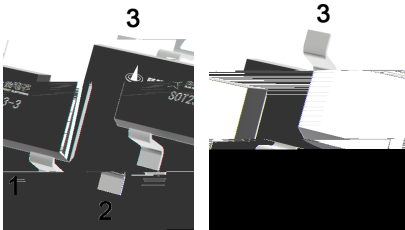
/ Applications

Medium power amplifier applications, Meet the stringent requirements of automotive applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Emitter PIN 3 Collector

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	Q	R
h_{FE} Range	120~270	180~390
Marking	QAKQ	QAKR

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Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-500	mA

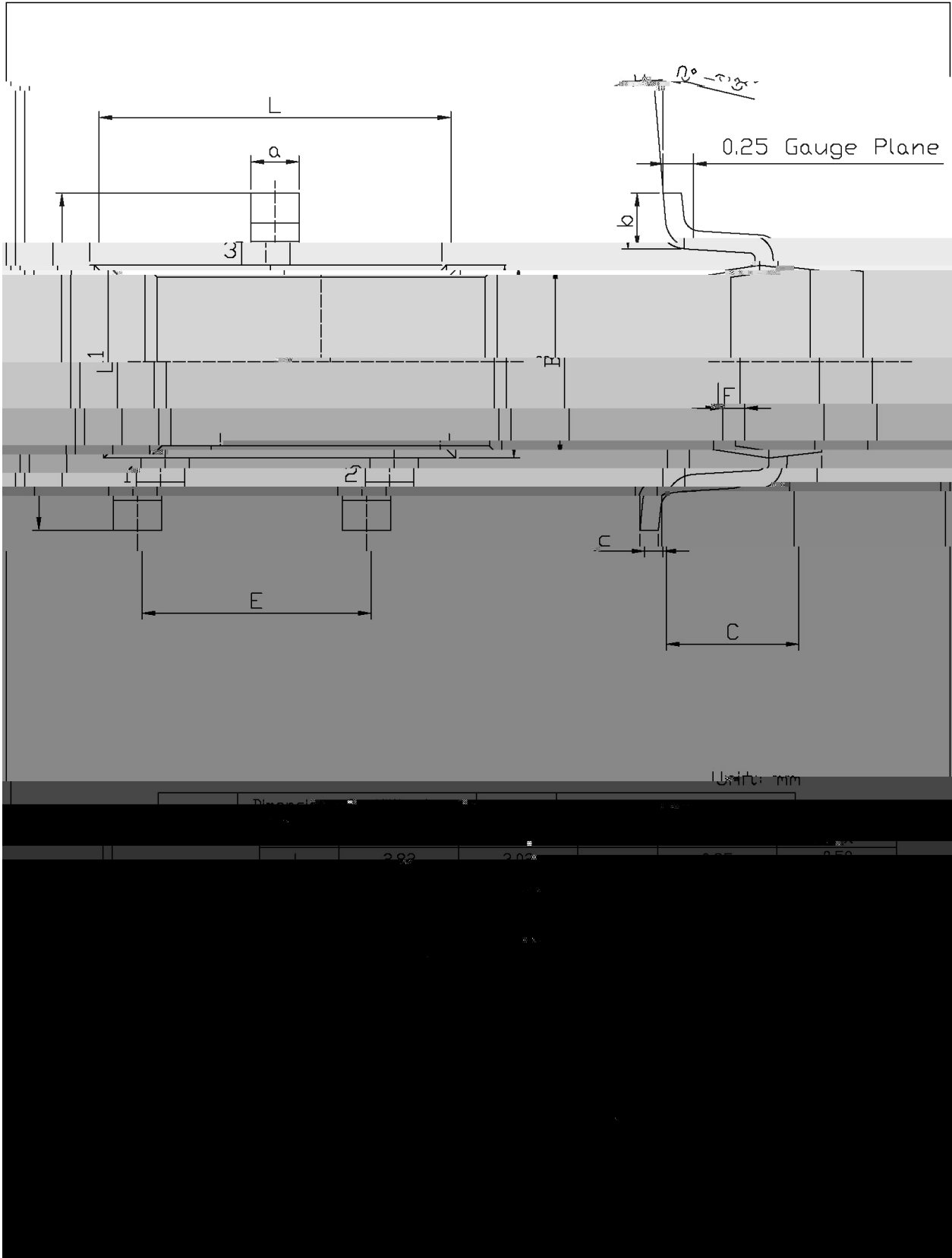
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DATA SHEET



/ Package Dimensions



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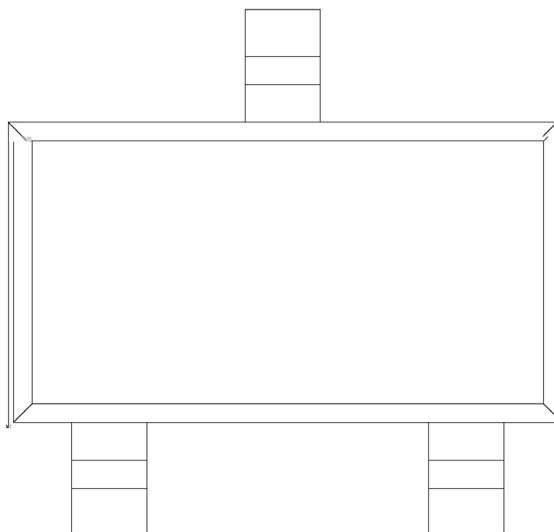


蓝箭电子
BLUE ROCKET ELECTRONICS

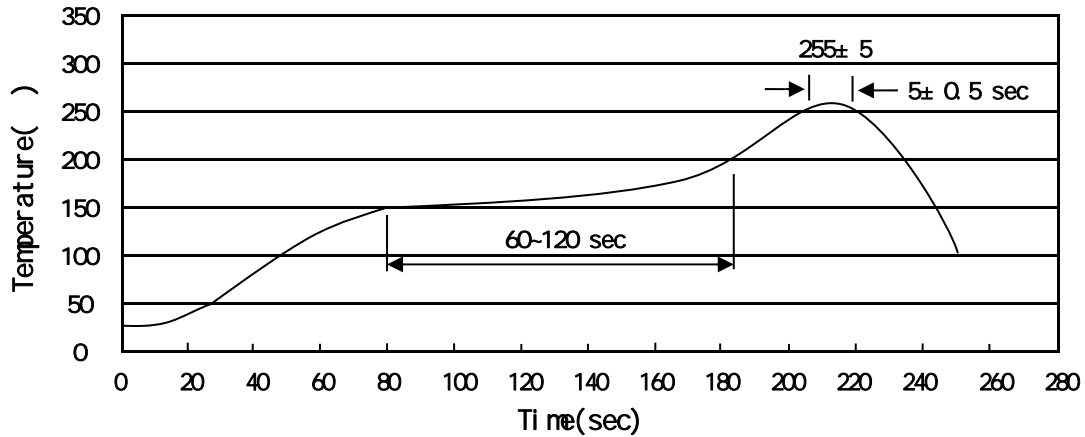
DATA SHEET

/ Marking Instructions

①②③④⑤⑥⑦⑧⑨⑩⑪⑫⑬⑭⑮⑯⑰⑱⑲⑳㉑㉒㉓㉔㉕㉖㉗㉘㉙㉚㉛㉜㉝㉞㉟㊱㊲㊳㊴㊵㊶㊷㊸㊹㊺



() / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- 1 150 200 60 120sec; 1.Preheating:150~200 , Time:60~120sec.
- 2 255±5 5±0.5sec; 2.Peak Temp.:255±5 , Duration:5±0.5sec.
- 3 2 10 /sec. 3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
SOT23-3	3,000	10	30,000	4	120,000	7 x8	210x205x205	445x230x435

/ Notices